

800V N-Channel MOSFET

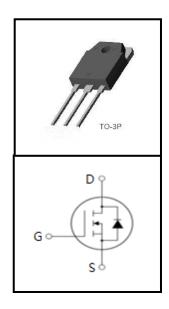
FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Package Mar			
CS14N80V	TO-3P	CS14N80V		



Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted						
Parameter	Symbol	Value	l lmi4			
Parameter		TO-3P	Unit			
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	800	>			
Continuous Drain Current	I _D	14	Α			
Pulsed Drain Current (note1)	I _{DM}	56	Α			
Gate-Source Voltage	V_{GSS}	±30	٧			
Single Pulse Avalanche Energy (note2)	E _{AS}	720	mJ			
Avalanche Current (note1)	I _{AS}	12	Α			
Repetitive Avalanche Energy (note1)	E _{AR}	432	mJ			
Power Dissipation (T _C = 25°C)	P_{D}	70	W			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C			

Thermal Resistance			
Parameter	Comple ed	Value	11
	Symbol	TO-3P	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	1.78	K/W
Thermal Resistance, Junction-to-Ambient	R _{thJA} 60		r\/VV



Specifications T _J = 25°C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Value			Unit		
	Syllibol	rest conditions	Min.	Тур.	Max.	Offic		
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800			V		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 800V, V_{GS} = 0V, T_{J} = 25^{\circ}C$	-		1	μΑ		
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30V$	1		±100	nA		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	V		
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_{D} = 7A$		0.6	0.72	Ω		
Dynamic								
Input Capacitance	C _{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1.0MHz$		2574		pF		
Output Capacitance	C _{oss}			264				
Reverse Transfer Capacitance	C _{rss}			50				
Total Gate Charge	Q_g	$V_{DD} = 640V, I_{D} = 14A,$ $V_{GS} = 10V$		105		nC		
Gate-Source Charge	Q_{gs}			12				
Gate-Drain Charge	Q_{gd}	65		58				
Turn-on Delay Time	t _{d(on)}	$V_{DD} = 400V, I_{D} = 14A,$ $R_{G} = 25 \Omega$		54.5		ns		
Turn-on Rise Time	t _r			51.5				
Turn-off Delay Time	t _{d(off)}			429				
Turn-off Fall Time	t _f			93				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	Is	_			14	A		
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			56			
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C$, $I_{SD} = 7A$, $V_{GS} = 0V$			1.4	V		
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_{S} = 14A,$		629		ns		
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /μs		3.2		μC		

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$
- 3. Pulse Test: Pulse width ≤ 300µs, Duty Cycle ≤ 1%



Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^{\circ}C$)

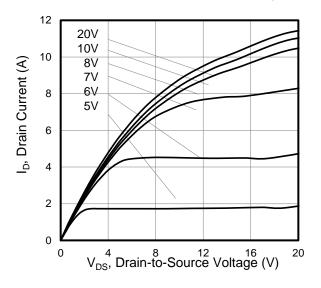


Figure 3. Drain Current vs. Temperature

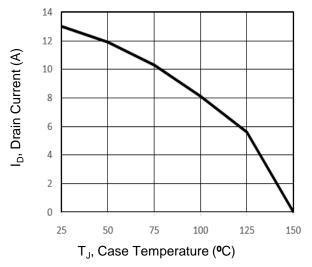


Figure 5. Transfer Characteristics

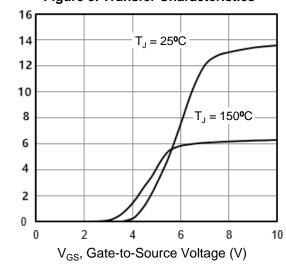


Figure 2. Body Diode Forward Voltage

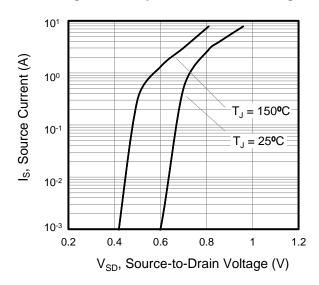


Figure 4. BV_{DSS} Variation vs. Temperature

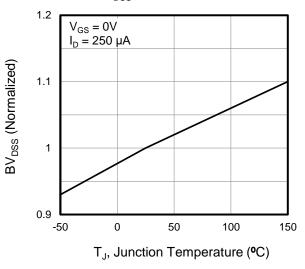
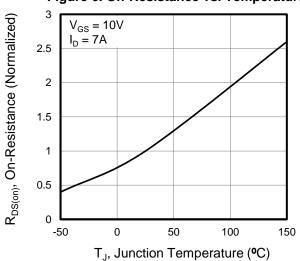


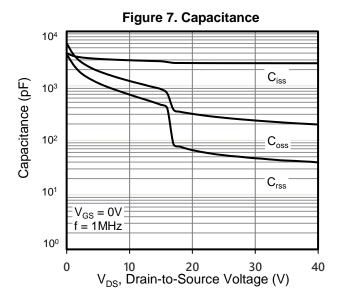
Figure 6. On-Resistance vs. Temperature



l_D, Drain Current (A)



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted



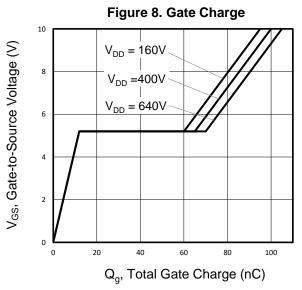


Figure 9. Transient Thermal Impedance

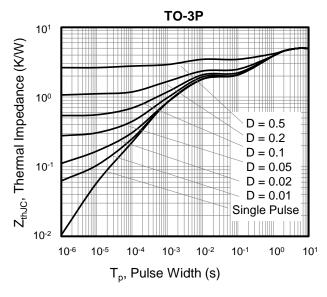




Figure A: Gate Charge Test Circuit and Waveform

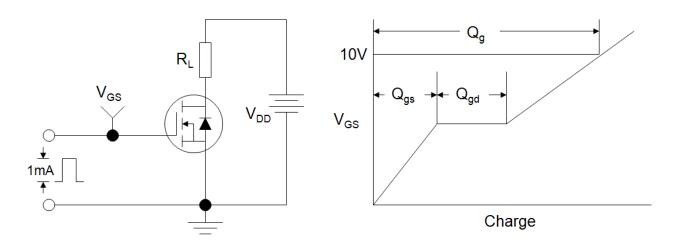


Figure B: Resistive Switching Test Circuit and Waveform

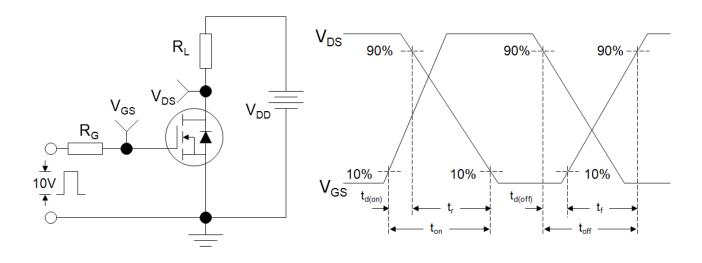
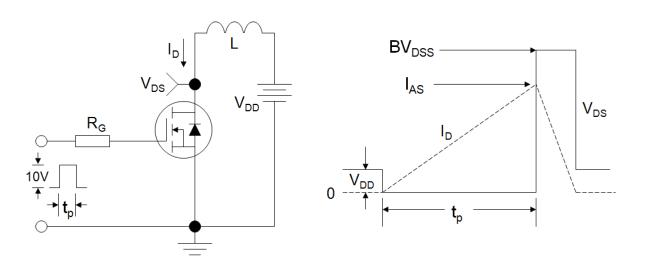
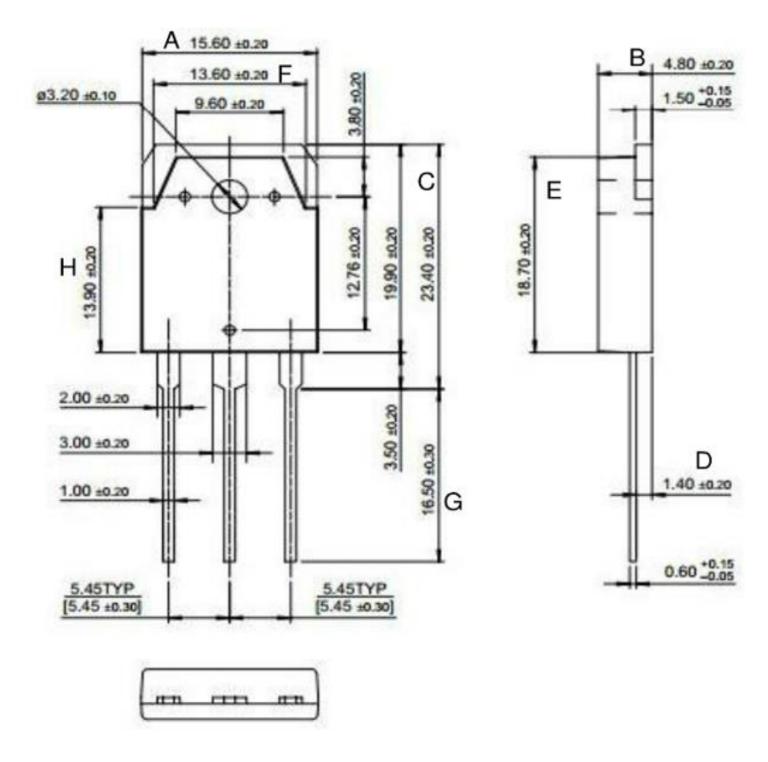


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-3P





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